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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICA	Ha	Hammond et al.			
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		FILING DATE: March 10, 2004 GROUP: 2812							
U.S. PATENT DOCUMENTS									
EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	AME			SUB CLASS	FILING DATE IF APPROPRIATE	
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	FILING DATE	ONLY LA		ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) INIT.									
C79 Request for Inter Partes Reexamination of U.S. Patent No. 6,900,094, filed August 2, 2006.									
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ASC-057C1 ATTORNEY DOCKET NO.: **FORM PTO - 1449** Hammond et al. SECOND SUPPLEMENTAL INFORMATION APPLICANT(S): **DISCLOSURE STATEMENT** SERIAL NO.: 10/797,231 FILING DATE: March 10, 2004 GROUP: 2812 U.S. PATENT DOCUMENTS EXAM. DOCUMENT DATE NAME **CLASS** SUB FILING DATE IF INIT. NUMBER **CLASS** APPROPRIATE A67 5,417,180 5/23/1995 Nakamura FOREIGN PATENT DOCUMENTS ENGLISH **DOCUMENT** DATE COUNTRY CLASS **FILING** ABSTRACT EXAM. NUMBER LANG INIT. CODE DATE ONLY CLASS (Y/N) OTHER ART, JOURNAL ARTICLES, ETC. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) EXAM. INIT. Chang, G.K., et al., "Selective Etching of SiGe on SiGe/Se Heterostructures," J. ELECTROCHEM. SOC. (1999) 138(1):202-04. Ismail, K., "Si/SiGe High-Speed Field Effect Transistors," IEEE IEDM TECH. DIG. (1995) 509-12. C75 C76 LeGoues, F.K. et al., "Oxidation studies of SiGe," J. APPL. PHYS. (1989) 65(4): 1724-28. Rhee, S.S., et al., "SiGe Resonant Tunneling Hot Carrier Transistor," IEEE IEDM TECH. DIG. (1999) 651-54. C78 Wolf, S., SILICON PROCESSING FOR THE VLSI ERA: VOL.2-PROCESS INTEGRATION (1990) Lattice Press, 66-83. **DATE CONSIDERED EXAMINER** LIBC/2825814.1